**Features**
- Frequency: 0.1-18GHz
- Small Signal Gain: 15.5dB
- Noise Figure: 1.5dB typ./2.0dB max.
- P1dB: 18dBm
- Power Supply: +5V/35mA
- Input/Output: 50Ω
- Die Size: 1.0 x 0.8 x 0.1 mm

**Typical Applications**
- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

**Functional Block Diagram**

**Electrical Specifications**
TA = +25°C, Vd = +5V

<table>
<thead>
<tr>
<th>Parameters</th>
<th>Min.</th>
<th>Typ.</th>
<th>Max.</th>
<th>Units</th>
</tr>
</thead>
<tbody>
<tr>
<td>Frequency</td>
<td>0.1-18</td>
<td></td>
<td></td>
<td>GHz</td>
</tr>
<tr>
<td>Small Signal Gain</td>
<td>14.5</td>
<td>15.5</td>
<td>17</td>
<td>dB</td>
</tr>
<tr>
<td>Gain Flatness</td>
<td>±1.75</td>
<td></td>
<td></td>
<td>dB</td>
</tr>
<tr>
<td>Noise Figure</td>
<td>-</td>
<td>1.5</td>
<td>2.0</td>
<td>dB</td>
</tr>
<tr>
<td>Output 1dB Compression (P1dB)</td>
<td>17</td>
<td>18</td>
<td>18.5</td>
<td>dBm</td>
</tr>
<tr>
<td>Input Return Loss</td>
<td>16</td>
<td>18</td>
<td>-</td>
<td>dB</td>
</tr>
<tr>
<td>Output Return Loss</td>
<td>13</td>
<td>19</td>
<td>-</td>
<td>dB</td>
</tr>
<tr>
<td>Static current</td>
<td></td>
<td>35</td>
<td></td>
<td>mA</td>
</tr>
</tbody>
</table>
**Outline Drawing:**
All Dimensions in μm

---

**Pad Description**

<table>
<thead>
<tr>
<th>Pad</th>
<th>Function</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>RF IN, Vg</td>
<td>RF signal input terminal; Amplifier gate bias, external 56nH winding inductor and 100pF bypass capacitor required; DC blocking capacitor required.</td>
</tr>
<tr>
<td>2</td>
<td>RF OUT, Vd</td>
<td>RF signal output terminal; Amplifier drain bias, external 56nH winding inductor and 100pF bypass capacitor required; DC blocking capacitor required.</td>
</tr>
<tr>
<td>Die bottom</td>
<td>GND</td>
<td>Die bottom must be connected to RF/DC ground.</td>
</tr>
</tbody>
</table>
MML061

GaAs MMIC
Low Noise Amplifier
0.1-18GHz

Assembly Drawing

Notes:
1. Die thickness: 100um
2. Typical bond pad is 100*100 μm²
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:
1. Maximum drain voltage: +7V
2. Maximum input power: +20dBm
3. Operating temperature: -55°C to +85°C
4. Storage temperature: -65°C to +150°C